

Ci  
cont

wherein said step of introducing N atoms into said gate oxide film comprises a thermal annealing process of said gate oxide film conducted in an atmosphere containing N atoms and O atoms.

Claim 8, line 1, change "7" to -6-.

sub  
D2 7  
9. (Twice Amended) A method as claimed in claim [7] 6, wherein said atmosphere contains N<sub>2</sub>O and said thermal annealing process is conducted at a temperature of about 900°C.

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C  
10. (Twice Amended) A method of fabricating a semiconductor device [as claimed in claim 6], comprising the steps of:

forming a gate oxide film on a substrate;

forming a gate electrode pattern on said gate oxide film; and

introducing N atoms into said gate oxide film while using said gate electrode pattern as a mask,

wherein said step of introducing N atoms into said gate oxide film includes an ion implantation process of N ions.